

Si Photo-diode Chip—TKB060PDN

1. Scope

- The specification applies to blue pass PIN silicon photo-diode chips.
- Type : TKB060PDN.

2. Structure

- PIN planar type.
- Electrode topside (anode) : Aluminum.
- Electrode backside (cathode) : Gold.

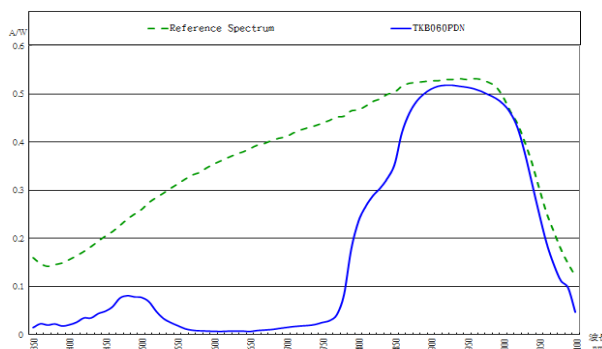
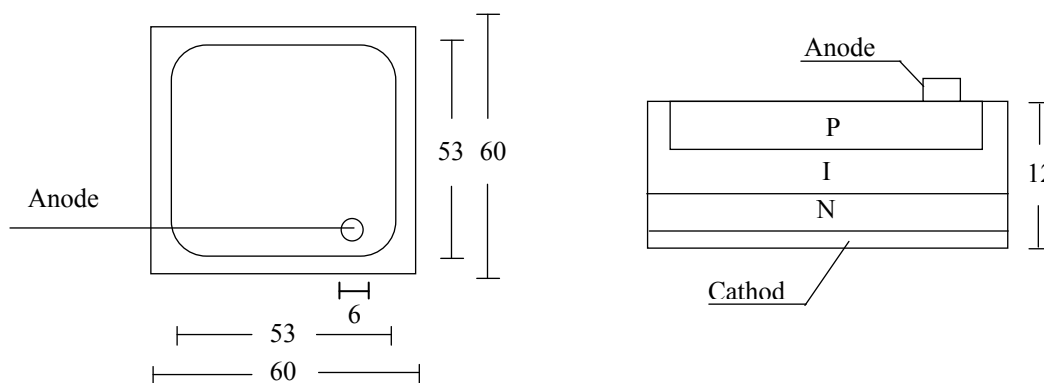
3. Size

- Chip size : 60mil × 60mil ± 1.5mil (1.52mm × 1.52mm ± 0.038mm)
- Thickness : 12mil ± 1mil (0.300mm ± 0.025mm)
- Active area : 53mil × 53mil ± 0.5mil (1.35mm × 1.35mm ± 0.013mm)
- Pad size : diameter 6mil ± 0.4mil (0.152mm ± 0.01mm)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V_F	$I_F = 10\text{mA}$, $H=0$	0.5		1.3	V
Reverse Breakdown Voltage	V_{BR}	$I_R = 100\mu\text{A}$, $H=0$	35			V
Reverse Dark Current	I_D	$V_R = 10\text{V}$, $H=0$		2	10	nA
Peak Sensitivity Wavelength of blue pass	λ_p			470		nm



Unit : mil

fig. 1

2016.Mar



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